

AO4702
N-Channel Enhancement Mode Field Effect Transistor with Schottky Diode
General Description

The AO4702 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky Diode is packaged in parallel to improve device performance in synchronous rectification applications, or H-bridge configurations. *Standard Product AO4702 is Pb-free (meets ROHS & Sony 259 specifications). AO4702L is a Green Product ordering option. AO4702 and AO4702L are electrically identical.*

Features

$V_{DS} = 30V$
 $I_D = 11A (V_{GS} = 10V)$
 $R_{DS(ON)} < 16m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 25m\Omega (V_{GS} = 4.5V)$

SCHOTTKY

$V_{DS} = 30V, I_F = 3A, V_F < 0.5V @ 1A$


Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	11	A
		$T_A=70^\circ C$	9.3	
Pulsed Drain Current ^B	I_{DM}	50		
Schottky reverse voltage	V_{KA}		30	V
Continuous Forward Current ^A	I_F	$T_A=25^\circ C$	4.4	A
		$T_A=70^\circ C$	3.2	
Pulsed Diode Forward Current ^B	I_{FM}		30	
Power Dissipation	P_D	$T_A=25^\circ C$	3	W
		$T_A=70^\circ C$	2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: MOSFET					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	31	40	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		59	75	°C/W
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	16	24	°C/W

Thermal Characteristics: Schottky					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	36	40	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		67	75	°C/W
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	25	30	°C/W

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F: The Schottky appears in parallel with the MOSFET body diode, even though it is a separate chip. Therefore, we provide the net forward drop, capacitance and recovery characteristics of the MOSFET and Schottky. However, the thermal resistance is specified for each chip separately.

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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current (Set by Schottky leakage)	$V_R=30\text{V}$		0.007	0.05	mA
		$V_R=30\text{V}$, $T_J=125^\circ\text{C}$		3.2	10	
		$V_R=30\text{V}$, $T_J=150^\circ\text{C}$		12	20	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.8	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=11\text{A}$		13.4	16	m Ω
		$T_J=125^\circ\text{C}$		16.8	21	
		$V_{GS}=4.5\text{V}$, $I_D=8\text{A}$		20	25	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=11\text{A}$		25		S
V_{SD}	Diode + Schottky Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.45	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		1040	1250	pF
C_{oss}	Output Capacitance (FET+Schottky)			212		pF
C_{rss}	Reverse Transfer Capacitance			121		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.7	0.85	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=11\text{A}$		19.8	24	nC
$Q_g(4.5\text{V})$	Total Gate Charge			9.8	12	nC
Q_{gs}	Gate Source Charge			2.5		nC
Q_{gd}	Gate Drain Charge			3.5		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.35\Omega$, $R_{GEN}=3\Omega$		4.5	7	ns
t_r	Turn-On Rise Time			3.9	7	ns
$t_{D(off)}$	Turn-Off Delay Time			17.4	30	ns
t_f	Turn-Off Fall Time			3.2	5.7	ns
t_{rr}	Body Diode + Schottky Reverse Recovery Time		$I_F=11\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		19	23
Q_{rr}	Body Diode + Schottky Reverse Recovery Charge	$I_F=11\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		9	11	nC

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

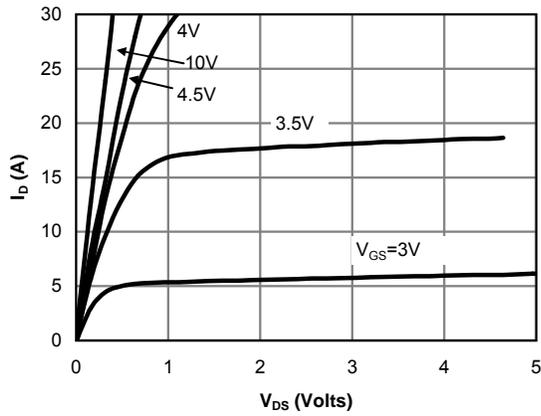


Fig 1: On-Region Characteristics

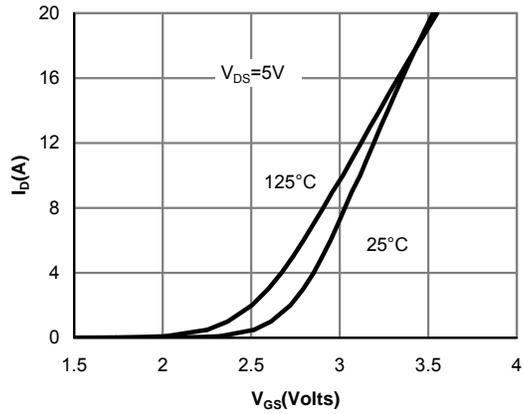


Figure 2: Transfer Characteristics

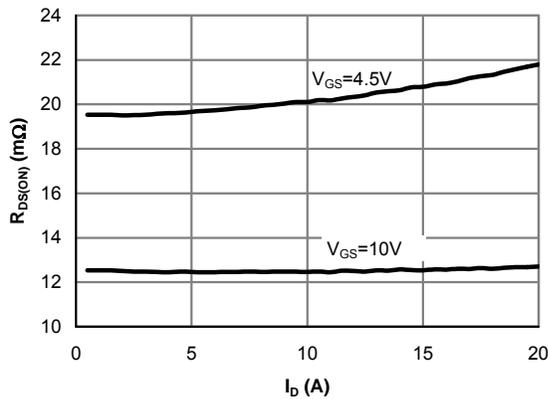


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

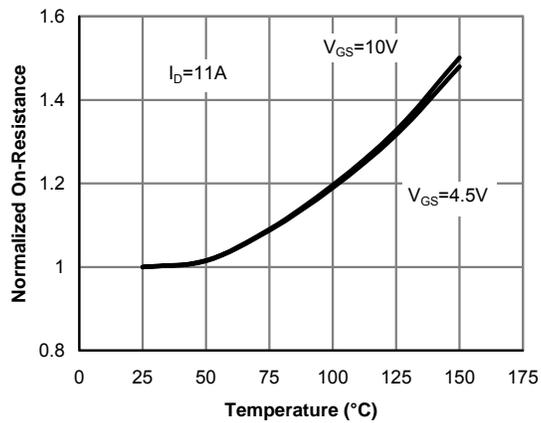


Figure 4: On-Resistance vs. Junction Temperature

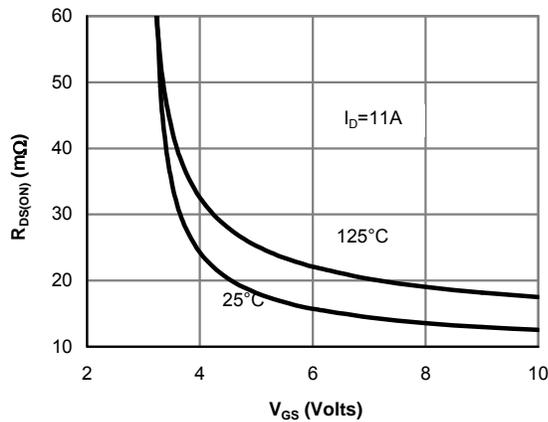


Figure 5: On-Resistance vs. Gate-Source Voltage

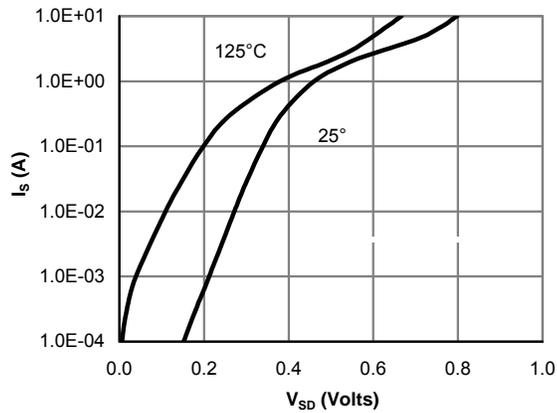


Figure 6: Body-Diode Characteristics

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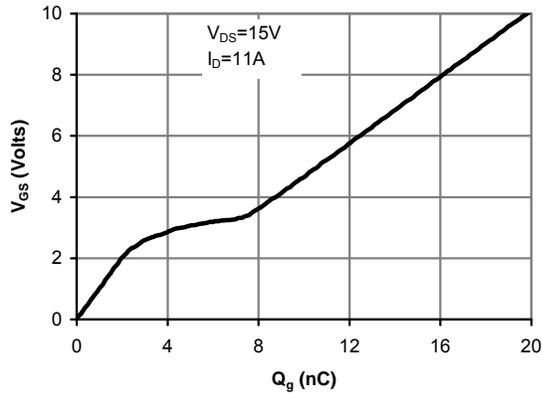


Figure 7: Gate-Charge Characteristics

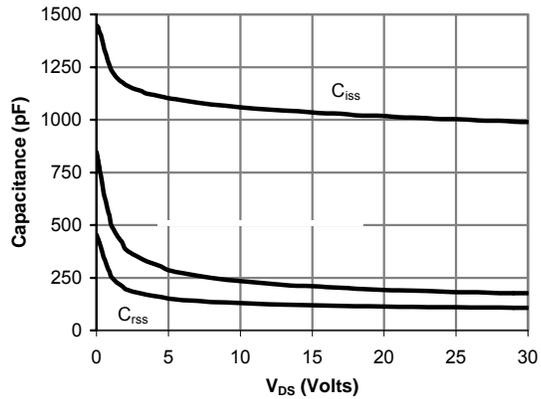


Figure 8: Capacitance Characteristics

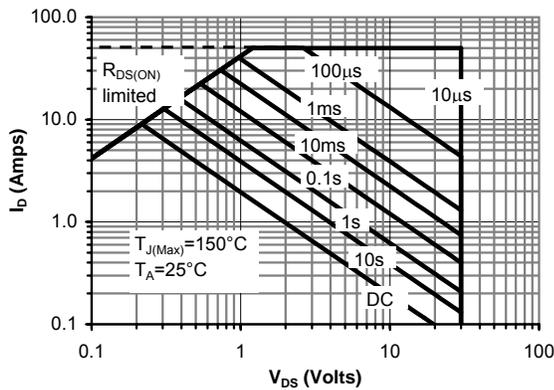


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

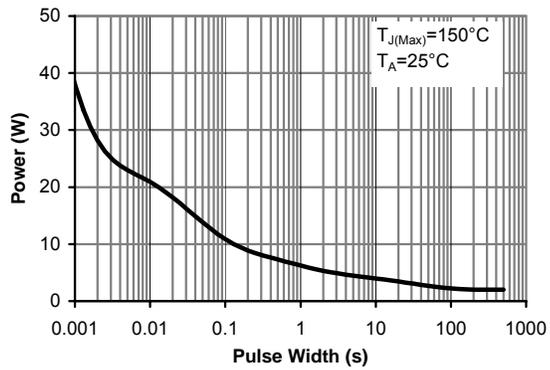


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

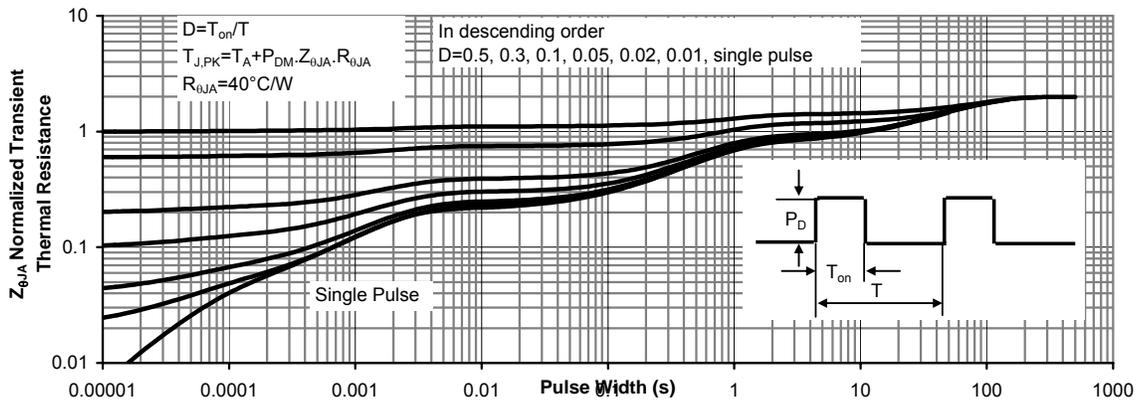


Figure 11: Normalized Maximum Transient Thermal Impedance